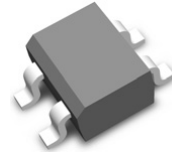


Bridge Rectifiers, 0.5 A

MB1S-MB8S



SOIC4 W
CASE 751EP

Description

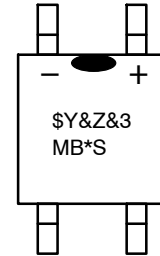
The MB family of bridge rectifiers is a 0.5 A rectifier family that achieves high surge current absorption within a very small foot print. Within its small 35 mm² form factor, the MB family shines in its surge capability. In order to absorb high surge currents, the design supports a 35 A I_{FSM} rating and a 5.0 A²Sec I²T rating. Devices in the family are also rated to breakdown voltages of up to 1000 V. These features make the MB family ideal for small power supplies that need a little extra surge capability.

For higher I_{FAV} current ratings, lower profile packaging, or lower V_F values, explore the **onsemi** MDB family of bridge rectifiers. For improved V_F and efficiency values in the MB package or even higher surge capability, ask about **onsemi**'s pending MBxSV family.

Features

- Low-Leakage
- Surge Overload Rating: 35 A peak
- Ideal for Printed Circuit Board
- UL Certified: UL #E258596
- This Device is Pb-Free and RoHS Compliant

MARKING DIAGRAM



- \$Y = Logo
- &Z = Assembly Plant Code
- &3 = 3-Digit Data Code (Year & Week)
- MB*S = Specific Device Code
- * = 1/2/4/6/8

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MB1S–MB8S

ABSOLUTE MAXIMUM RATINGS

(Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	MB1S	MB2S	MB4S	MB6S	MB8S	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage	100	200	400	600	800	V
V_{RMS}	Maximum RMS Bridge Input Voltage	70	140	280	420	560	V
V_R	DC Reverse Voltage (Rated V_R)	100	200	400	600	800	V
$I_{F(AV)}$	Average Rectified Forward Current at $T_A = 50^\circ\text{C}$	0.5					A
I_{FSM}	Non-Repetitive Peak Forward Surge Current: 8.3 ms Single Half-Sine-Wave	35					A
T_{STG}	Storage Temperature Range	-55 to +150					$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to +150					$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	1.4	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, per Leg (Note 1)	85	$^\circ\text{C}/\text{W}$
$R_{\theta JL}$	Thermal Resistance, Junction to Lead, per Leg (Note 1)	20	$^\circ\text{C}/\text{W}$

1. Device mounted on PCB with 0.5×0.5 inch (13×13 mm) lead length.

ELECTRICAL CHARACTERISTICS (Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Value	Unit
V_F	Forward Voltage, per Bridge	$I_F = 0.5 \text{ A}$	1.0	V
I_R	Reverse Current, per Leg at Rated V_R	$T_A = 25^\circ\text{C}$	5.0	μA
		$T_A = 125^\circ\text{C}$	0.5	mA
I^2t	I^2t Rating for Fusing	$t < 8.3 \text{ ms}$	5.0	A^2s
C_T	Total Capacitance, per Leg	$V_R = 4.0 \text{ V}, f = 1.0 \text{ MHz}$	13	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
MB1S	MB1S	SOIC4 W (Pb-Free)	3,000 / Tape & Reel
MB2S	MB2S		
MB4S	MB4S		
MB6S	MB6S		
MB8S	MB8S		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL PERFORMANCE CHARACTERISTICS

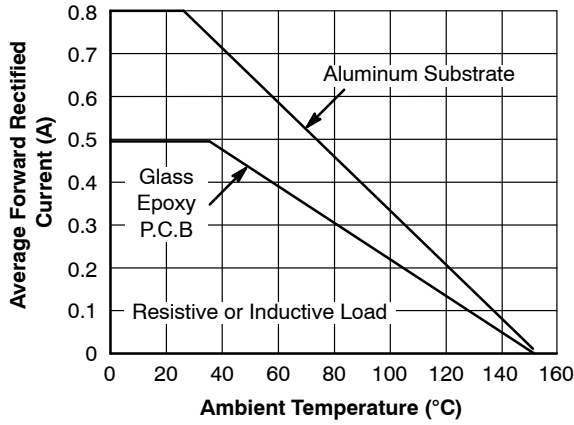


Figure 1. Derating Curve for Output Rectified Current

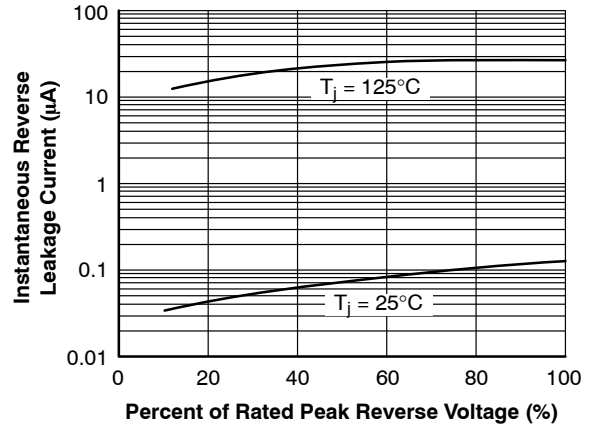


Figure 2. Typical Reverse Leakage Characteristics Per Leg

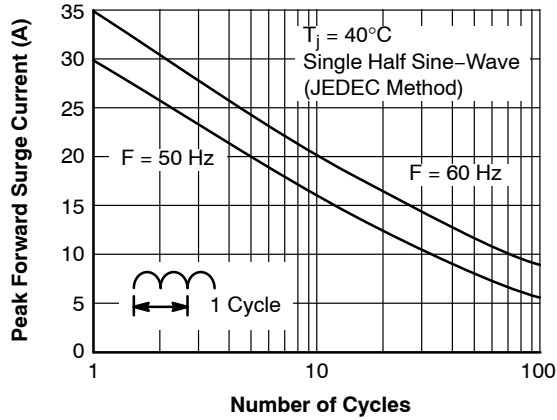


Figure 3. Maximum Non-Repetitive Peak Forward Surge Current Per Leg

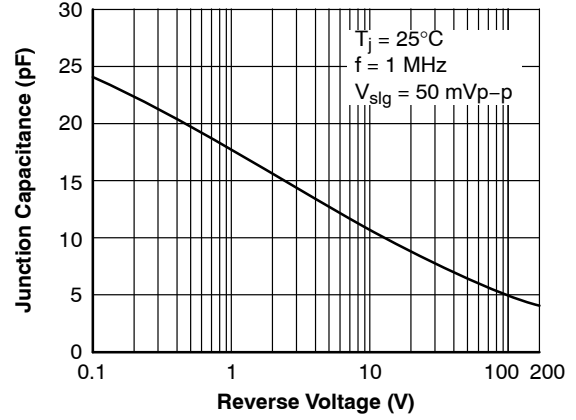


Figure 4. Typical Junction Capacitance Per Leg

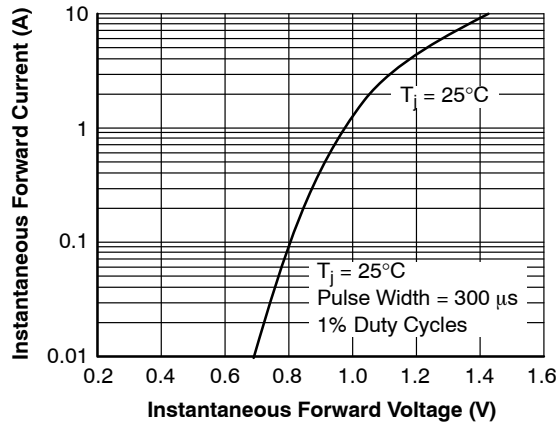


Figure 5. Typical Forward Voltage Characteristics Per Leg

MECHANICAL CASE OUTLINE

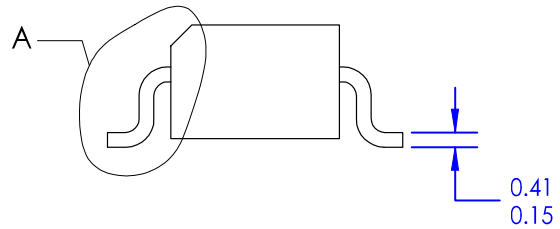
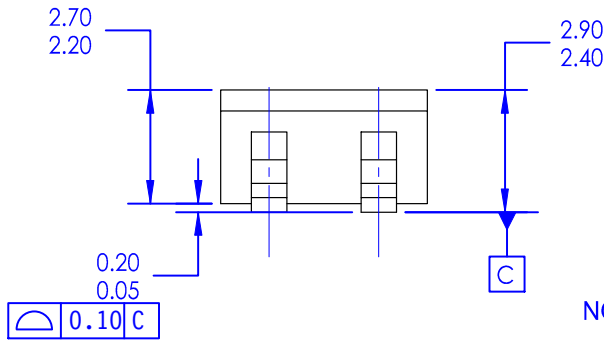
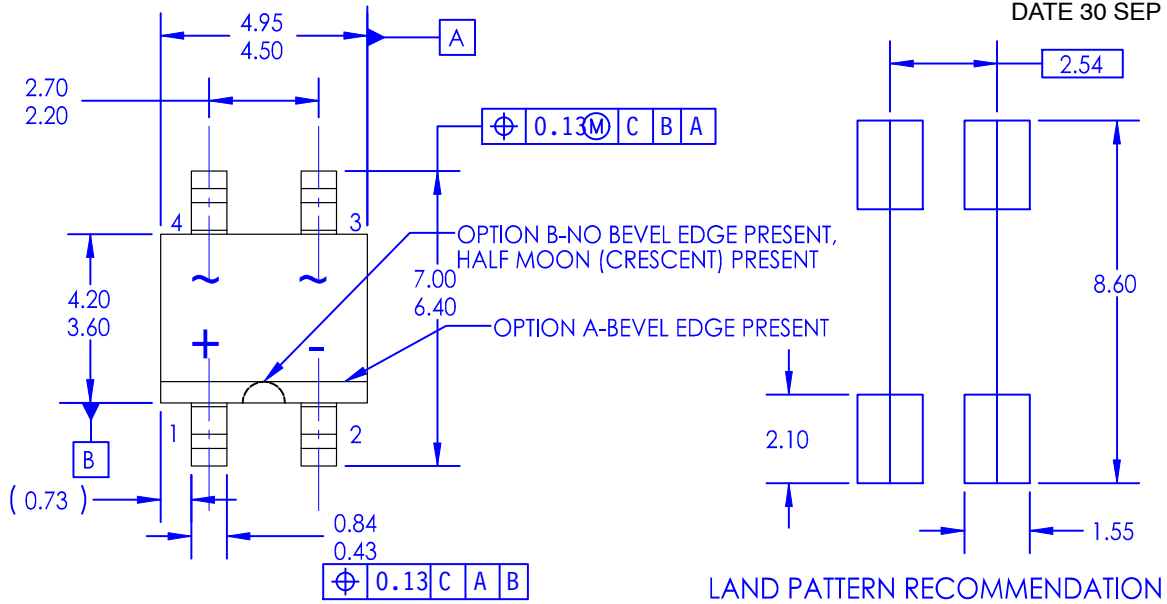
PACKAGE DIMENSIONS

ON Semiconductor®



SOIC4 W CASE 751EP ISSUE O

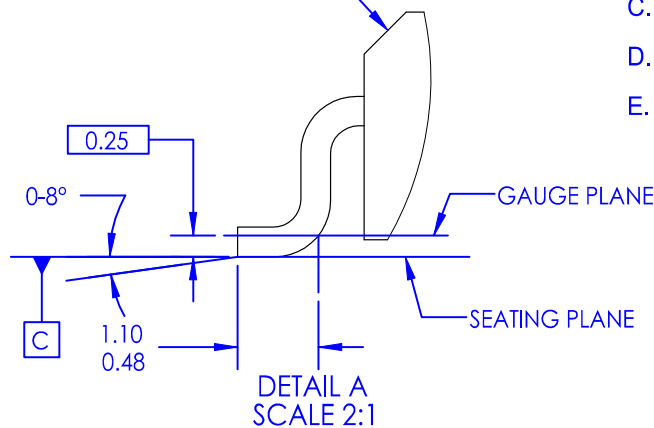
DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

- A. THIS PACKAGE DOES NOT CONFORM TO JEDEC TO269AA
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D. DIMENSIONS AND TOLERANCES AS PER ASME Y14.5-2009.
- E. LAND PATTERN AS PER IPC7351# SOIC254P960X400-4N

OPTION A - BEVEL EDGE



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DESCRIPTION:	SOIC4 W	PAGE 1 OF 1

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